

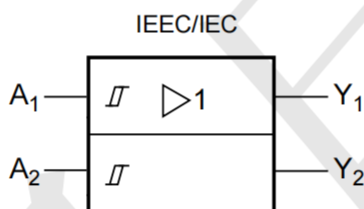
Features

- Operate From 1.65V to 5.5V
- 5 V tolerant input/output for interfacing with 5 V logic
- $\pm 24\text{mA}$ output drive ($V_{CC} = 3.3\text{V}$)
- CMOS low-power consumption and high noise immunity
- OFF Supports Partial-Power-Down Mode Operation
- Latch-up performance exceeds 100mA
- Specified from $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$
- ESD Protection Exceeds JESD 22
 - 2000-V Human-Body Model (A114-A)
 - 1000-V Charged-Device Model (C101)
- SOT363 Package Available

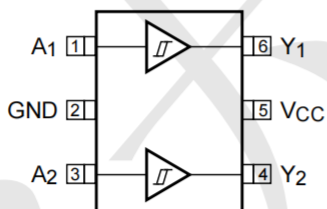
General Description

The NC7WZ17P6X is a high-performance, low-power, low-voltage, Si-gate CMOS device which provides two independent buffers with Schmitt trigger action. It is capable of transforming slowly changed input signals into sharply defined, jitter-free output signals.

Logic Diagram



Pin Configuration



Marking: Z17Y

Function Table

INPUT(A)	OUTPUT(Y)
L	L
H	H

H=High Level
L=Low Level

Absolute Maximum Ratings

PARAMETER	SYMBOL	RATINGS	UNIT
Supply Voltage	V_{CC}	-0.5 ~ 6.5	V
Input Voltage (Note 2)	V_{IN}	-0.5 ~ 6.5	V
Output Voltage (Note 2,3)	High-Impedance	-0.5 ~ 6.5	V
	Power-Off State		
	High State	-0.5 ~ $V_{CC}+0.5$	V
	Low State		
Input Clamp Current ($V_{IN}<0$)	I_{IK}	-50	mA
Output Clamp Current ($V_{OUT}<0$)	I_{OK}	-50	mA
Output Current	I_{OUT}	± 50	mA
V_{CC} or GND Current	I_{CC}	± 100	mA
Junction Temperature	T_J	+150	°C
Storage Temperature	T_{STG}	-65 ~ +150	°C

- Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.
3. The value of V_{CC} is provided in the recommended operating conditions table.

Recommended Operating Conditions

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Supply Voltage	V_{CC}	Operating	1.65		5.5	V
Input Voltage	V_{IN}		0		5.5	V
Output Voltage	V_{OUT}	High or low state	0		V_{CC}	V
High-Level Input Voltage	V_{T+}	$V_{CC} = 1.65$ V	0.70		1.40	V
		$V_{CC} = 2.3$ V	1.00		1.70	V
		$V_{CC} = 3.0$ V	1.30		2.20	V
		$V_{CC} = 4.5$ V	1.90		3.10	V
		$V_{CC} = 5.5$ V	2.20		3.70	V
Low-Level Input Voltage	V_{T-}	$V_{CC} = 1.65$ V	0.30		0.70	V
		$V_{CC} = 2.3$ V	0.40		1.00	V
		$V_{CC} = 3.0$ V	0.60		1.30	V
		$V_{CC} = 4.5$ V	1.10		2.00	V
		$V_{CC} = 5.5$ V	1.40		2.50	V
Hysteresis Voltage	ΔV_T	$V_{CC} = 1.65$ V	0.30		0.80	V
		$V_{CC} = 2.3$ V	0.40		0.90	V
		$V_{CC} = 3.0$ V	0.40		1.10	V
		$V_{CC} = 4.5$ V	0.60		1.30	V
		$V_{CC} = 5.5$ V	0.70		1.40	V
Operating Temperature	T_A		-40		+125	°C

Note: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation.



Electrical Characteristics ($T_A = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
High-Level Output Voltage	V_{OH}	$V_{CC}=1.65\text{V}\sim 5.5\text{V}$, $I_{OH}=-100\mu\text{A}$	V_{CC} -0.1			V
		$V_{CC}=1.65\text{V}$, $I_{OH}=-4\text{mA}$	1.20			V
		$V_{CC}=2.3\text{V}$, $I_{OH}=-8\text{mA}$	1.90			V
		$V_{CC}=3.0\text{V}$, $I_{OH}=-16\text{mA}$	2.40			V
		$V_{CC}=3.0\text{V}$, $I_{OH}=-24\text{mA}$	2.30			V
		$V_{CC}=4.5\text{V}$, $I_{OH}=-32\text{mA}$	3.80			V
Low-Level Output Voltage	V_{OL}	$V_{CC}=1.65\sim 5.5\text{V}$, $I_{OL}=100\mu\text{A}$			0.10	V
		$V_{CC}=1.65\text{V}$, $I_{OL}=4\text{mA}$			0.45	V
		$V_{CC}=2.3\text{V}$, $I_{OL}=8\text{mA}$			0.30	V
		$V_{CC}=3.0\text{V}$, $I_{OL}=16\text{mA}$			0.40	V
		$V_{CC}=3.0\text{V}$, $I_{OL}=24\text{mA}$			0.55	V
		$V_{CC}=4.5\text{V}$, $I_{OL}=32\text{mA}$			0.55	V
Input Leakage Current	$I_{I(LEAK)}$	$V_{IN}=0$ to 5.5V , $V_{CC}=0\sim 5.5\text{V}$			± 5	μA
Power OFF Leakage Current	I_{OFF}	V_{IN} or $V_{OUT}=5.5\text{V}$, $V_{CC}=0$			± 10	μA
Quiescent Supply Current	I_{CC}	$V_{IN}=V_{CC}$ or GND , $I_{OUT}=0$ $V_{CC}=1.65\sim 5.5\text{V}$			10	μA
Additional Quiescent Supply Current	ΔI_{CC}	One input at $V_{CC}-0.6\text{V}$ Other inputs at V_{CC} or GND , $I_{OUT}=0$, $V_{CC}=3\sim 5.5\text{V}$			500	μA
Input Capacitance	C_I	$V_{IN}=V_{CC}$ or GND , $V_{CC}=3.3\text{V}$		4		pF

Switching Characteristics ($T_A = 25^\circ\text{C}$, unless otherwise specified)

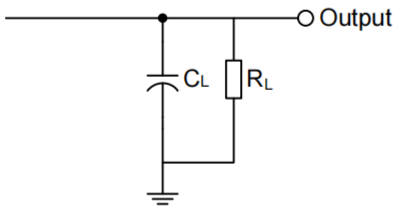
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Propagation delay nA to nY	t_{PLH} t_{PHL}	$V_{CC}=1.8\text{V}\pm 0.15\text{V}$, $C_L=30\text{pF}$, $R_L=1\text{K}\Omega$	3.9		9.3	ns
		$V_{CC}=2.5\text{V}\pm 0.2\text{V}$, $C_L=30\text{pF}$, $R_L=500\Omega$	1.9		5.7	ns
		$V_{CC}=3.3\text{V}\pm 0.3\text{V}$, $C_L=50\text{pF}$, $R_L=500\Omega$	2.2		5.4	ns
		$V_{CC}=5\text{V}\pm 0.5\text{V}$, $C_L=50\text{pF}$, $R_L=500\Omega$	1.5		4.3	ns

Operating Characteristics (Unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Power Dissipation Capacitance	C_{PD}	$V_{CC}=5\text{V}$, $f=10\text{MHz}$		21		pF



TEST CIRCUIT AND WAVEFORMS

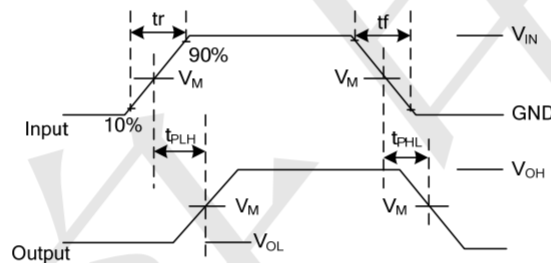


V_{CC}	V_{IN}	t_R, t_F	V_M	C_L	R_L
1.65V~1.95V	V_{CC}	$\leq 2\text{ns}$	$V_{CC}/2$	30pF	1k Ω
2.3V~2.7V	V_{CC}	$\leq 2\text{ns}$	$V_{CC}/2$	30pF	500 Ω
3.0V~3.6V	3V	$\leq 2.5\text{ns}$	1.5V	50pF	500 Ω
4.5V~5.5V	V_{CC}	$\leq 2.5\text{ns}$	$V_{CC}/2$	50pF	500 Ω

Definitions for test circuit:

R_L = Load resistance.

C_L = Load capacitance including jig and probe capacitance.



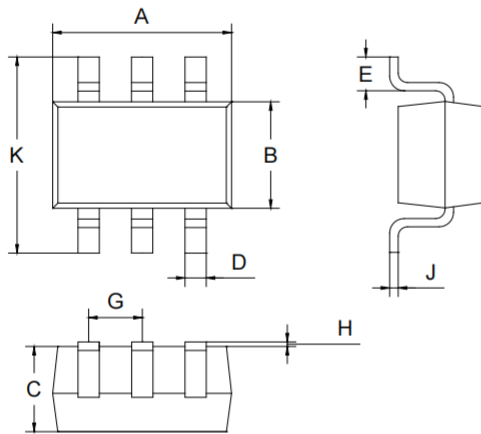
Notes: 1. V_{OL} and V_{OH} are typical output drop that occur with the output load.

2. t_{PLH} and t_{PHL} are the same as t_{PD} .



Package Outline Dimensions (Unit: mm)

SOT363



Dimension	Min.	Max.
A	2.00	2.20
B	1.15	1.35
C	0.85	1.05
D	0.15	0.35
E	0.25	0.40
G	0.60	0.70
H	0.02	0.10
J	0.05	0.15
K	2.20	2.40

Mounting Pad Layout (Unit: mm)

